

SB5560S 55A SOTs

FEATURES

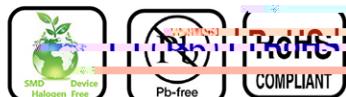
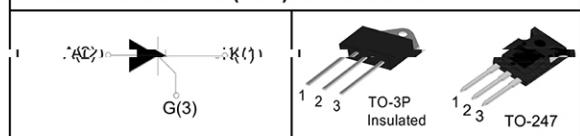
- High thermal cycling performance
- High voltage capacity
- Very high current surge capability

APPLICATIONS

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Parameters Summary

VD/VR:1200/1600V IT(RMS):55A IGT :60mA



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	value	Unit
Storage junction temperature range	T _{stg}	-40~150	°C
Operating junction temperature range	T _j	-40~125	°C
Repetitive peak off-state voltage (T=25°C)	V _{DRM}	1200/1600	V
Repetitive peak reverse voltage (T=25°C)	V _{RSM}	1200/1600	V
Non repetitive surge peak Off-state voltage	V _{DSM}	V _{DRM} +100	V
Non repetitive peak reverse voltage	V _{RSM}	V _{RSM} +100	V
RMS on-state current	I _{TSM}	55	A
TO-3PIs.(TC=80°C) TO-247(TC=85°C)	I _{T(AV)}	550	A
	I _{TSM}	550	A
Average on-state current (180° conduction angle)	I _{T(AV)}	550	A
I ² t value for fusing (tp=10ms)	I ² t	1500	A ² S
Critical rate of rise of on-state current (I=2×IGT, tr ≤ 100 ns)	di/dt	150	A/μS
Peak gate current	I _{GM}	5	A
Average gate power dissipation	P _{G(AV)}	2	W

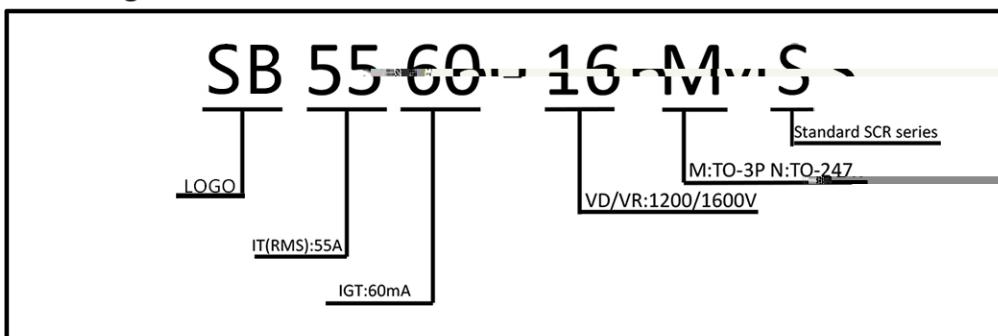
Thermal Resistances

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case (DC)	TO-3P	0.65
		TO-247	0.60

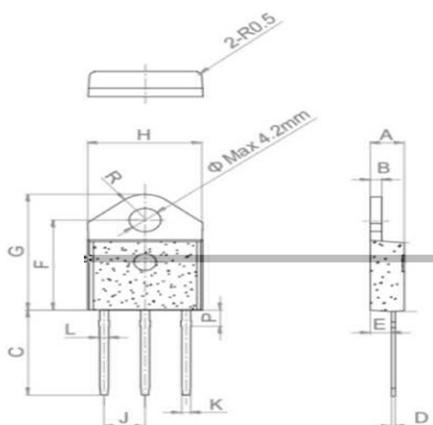
Symbol	Test Condition	MAX.	MIN.
I_{SD}	$V_D = 12V, T_J = 125^{\circ}C$	60	0
V_{DS}		80 mV	1.2 V
V_{GD}	$V_D = V_{DRM}, T_J = 125^{\circ}C$	MIN.	
I_S	$I_S = 1.2I_{SD}$	MAX.	
I_H	$I_H = 50mA$	MAX.	
dV/dt	$V_D = 2/3V_{DRM}$, Gate Open, $T_J = 125^{\circ}C$	MIN.	

Symbol	Value (MAX.)
V_{TM}	4
I_{DRM}	10
I_{RRM}	1

Ordering Information Scheme

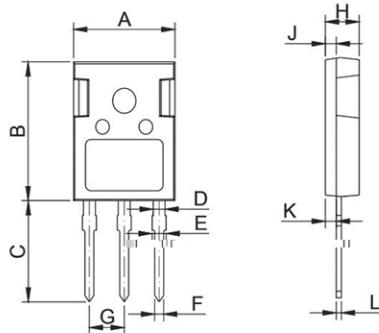


TO-3P Package Mechanical Data



Ref.	Constituents	Monomers	T _m	T _d
A	22.0%	4.00	-10	411
B	5.40	1.00	>300	400
C	48.40	1.00	-10	400
D	1.00	0.70	-10	402
E	1.00	0.00	-10	400
F	15.92	16.32	-10	412
G	1.00	0.00	-10	400
H	1.00	0.00	-10	400
I	5.85	214	-10	404
K	1.00	1.50	-10	401
L	1.00	1.35	-10	401
P	1.00	0.00	-10	400
R	1.00	0.65	-10	400

TO-247 Package Mechanical Data



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.50	15.80	16.16	0.61	0.62	0.64
B	20.80	21.00	22.20	0.82	0.82	0.84
C	19.70	20.00	20.30	0.776	0.787	0.799
D	1.80	2.00	2.20	0.071	0.073	0.079
E	1.90	2.10	2.30	0.075	0.083	0.091
F	1.00	1.20	1.40	0.039	0.047	0.055
G		5.44			0.214	0.224
H	4.30 ^a	5.00 ^b	5.20 ^c	0.169	0.201	0.205
J	1.90	2.00	2.10	0.075	0.079	0.083
K	2.20	2.35	2.50	0.087	0.093	0.098
L	0.41	0.60	0.79	0.016	0.024	0.031

FIG.1 Maximum power dissipation versus on-state current

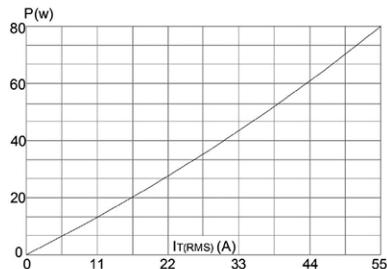


FIG.3: Surge peak on-state current versus number of cycles

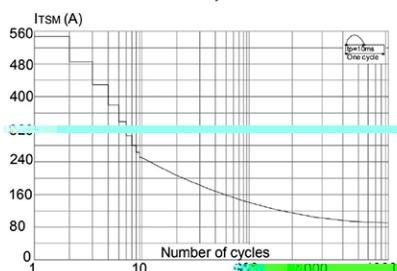


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of $I_2 t$

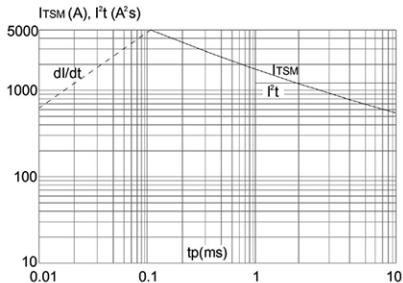


FIG.2: on-state currents versus case temperature

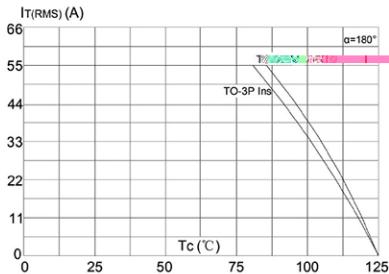


FIG.4: On-state characteristics (maximum values)

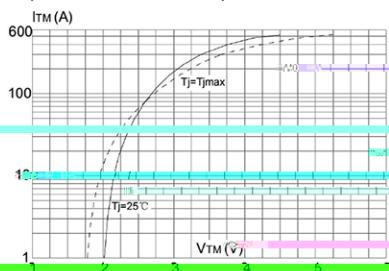


FIG.6: Relative variations of gate current, drain current, drain-to-source current and latching current versus junction temperature

